

In the Specification

Replace the Abstract on p. 27 with the paragraph shown below:

ABSTRACT OF THE DISCLOSURE

D' Semiconductor processing methods of forming transistors, semiconductor processing methods of forming dynamic random access memory circuitry, and related integrated circuitry are described. In one embodiment, active areas are formed over a substrate, with one of the active areas having a width of less than one micron, and with some of the active areas having different widths. A gate line is formed over the active areas to provide transistors having different threshold voltages. In one embodiment, the transistors are provided with different threshold voltages without using a separate channel implant for the transistors.

In the Claims

1. A semiconductor processing method of forming transistors comprising:

forming a plurality of shallow trench isolation regions received within a substrate, the shallow trench isolation regions being formed to define a plurality of active areas having widths within the substrate, some of the widths being no greater than about one micron, at least two of the widths being different; and

forming a gate line over respective active areas to provide individual transistors, the transistors corresponding to the active areas having the different widths having different threshold voltages.